

ABSTRACT OF THE DISCLOSURE

The invention can provide a solid-state imaging device that can include a pixel array where a plurality of unit pixels including a photo diode and an insulated gate field effect transistor for detecting photocharges are arranged, and a control circuit that controls the operation of the pixel array. The control circuit can cause a junction region between a semiconductor substrate of a first conductivity type and a semiconductor layer of a second conductivity type to be in a forward bias state so as to accumulate a predetermined amount of the charge of a predetermined conductivity type in an accumulation region, and control discharging the charges of a predetermined conductivity type accumulated in the accumulation region thereafter. Accordingly, the invention provides a solid-state imaging element that avoids deterioration of image quality caused by photocharges accumulated during previous imaging.